FUJI ELECTRIC

2SK2906-01

FAP-IIIB Series

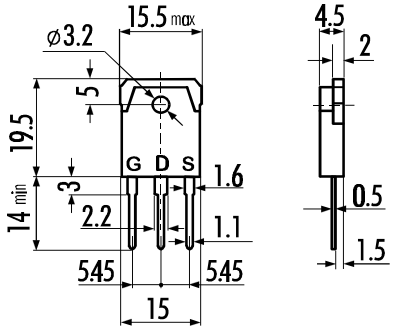
N-channel MOS-FET			
60V	7,8mΩ	±100A	150W

> Features

- High Current
- Low On-Resistance
- No Secondary Breakdown
- Low Driving Power
- Avalanche Rated

> Outline Drawing

TO-3P



> Applications

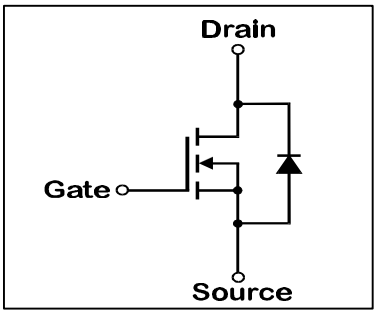
- Motor Control
- General Purpose Power Amplifier
- DC-DC converters

> Maximum Ratings and Characteristics

- Absolute Maximum Ratings (T_C=25°C), unless otherwise specified

Item	Symbol	Rating	Unit
Drain-Source-Voltage	V_{DS}	60	V
Continous Drain Current	I_D	±100	A
Pulsed Drain Current	$I_{D(puls)}$	±400	A
Gate-Source-Voltage	V_{GS}	±30	V
Maximum Avalanche Energy	E_{AV}	1268.3	mJ*
Max. Power Dissipation	P_D	150	W
Operating and Storage Temperature Range	T_{ch}	150	°C
	T_{stg}	-55 ~ +150	°C

L=0.169mH,Vcc=24V



- Electrical Characteristics (T_C=25°C), unless otherwise specified

Item	Symbol	Test conditions		Min.	Typ.	Max.	Unit
Drain-Source Breakdown-Voltage	BV_{DSS}	I_D=1mA V_{GS}=0V		60			V
Gate Threshhold Voltage	$V_{GS(th)}$	I_D=10mA V_{DS}=V_{GS}		2,5	3,0	3,5	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V	T_{ch}=25°C		10	500	µA
		V_{GS}=0V	T_{ch}=125°C		0,2	1,0	mA
Gate Source Leakage Current	I_{GSS}	V_{GS}=±30V V_{DS}=0V			10	100	nA
Drain Source On-State Resistance	$R_{DS(on)}$						mΩ
		I_D=50A	V_{GS}=10V		5,7	7,8	mΩ
Forward Transconductance	g_{fs}	I_D=50A V_{DS}=25V		25	55		S
Input Capacitance	C_{iss}	V_{DS}=25V			5400	8100	pF
Output Capacitance	C_{oss}	V_{GS}=0V			2100	3150	pF
Reverse Transfer Capacitance	C_{rss}	f=1MHz			550	830	pF
Turn-On-Time t_{on} (t_{on}=$t_{d(on)}$+t_r)	$t_{d(on)}$	V_{CC}=30V			29	50	ns
	t_r	V_{GS}=10V			200	350	ns
Turn-Off-Time t_{off} (t_{on}=$t_{d(off)}$+t_f)	$t_{d(off)}$	I_D=100A			160	240	ns
	t_f	R_{GS}=10 Ω			150	230	ns
Avalanche Capability	I_{AV}	L = 100µH T_{ch}=25°C		100			A
Diode Forward On-Voltage	V_{SD}	I_F=100A V_{GS}=0V T_{ch}=25°C			1,0	1,5	V
Reverse Recovery Time	t_{rr}	I_F=50A V_{GS}=0V			85		ns
Reverse Recovery Charge	Q_{rr}	-dI/dt=100A/µs T_{ch}=25°C			0,21		µC

- Thermal Characteristics

Item	Symbol		Min.	Typ.	Max.	Unit
Thermal Resistance	$R_{th(ch-c)}$	channel to case			0,83	°C/W
	$R_{th(ch-a)}$	channel to ambient			35,0	°C/W

N-channel MOS-FET				
60V		7,8mΩ	±100A	150W

2SK2906-01
FAP-IIIB Series

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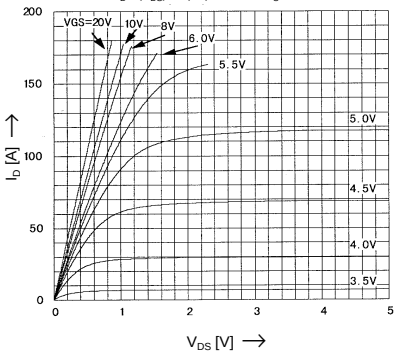
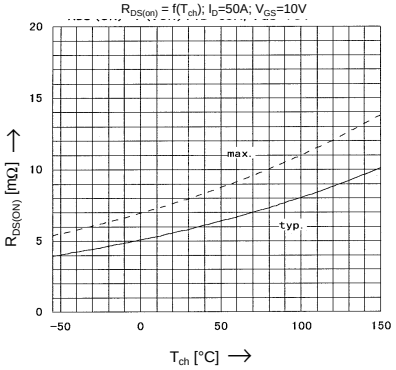
> Characteristics

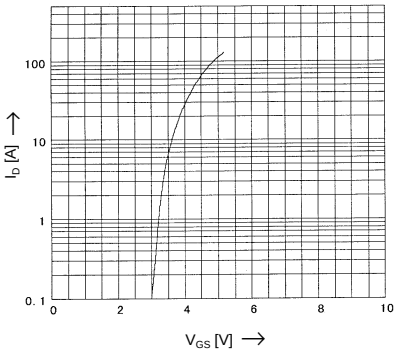
Typical Output Characteristics
I_D=f(V_{DS}); 80µs pulse test; T_C=25°C



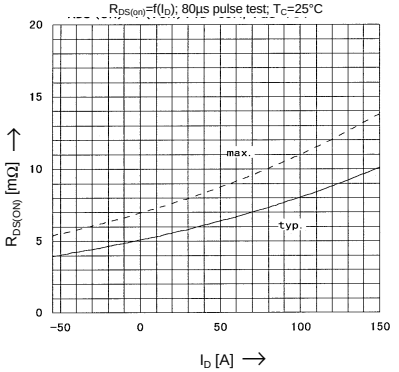
Drain-Source On-State Resistance vs. T_{ch}
$R_{DS(on)}$ = f(T_{ch}); I_D=50A; V_{GS}=10V



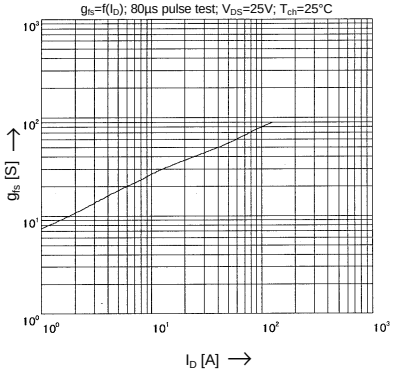
Typical Transfer Characteristics
I_D=f(V_{GS}); 80µs pulse test; V_{DS}=25V; T_{ch}=25°C



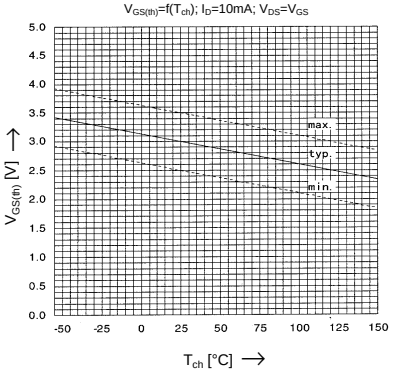
Typical Drain-Source On-State-Resistance vs. I_D
$R_{DS(on)}$=f(I_D); 80µs pulse test; T_C=25°C



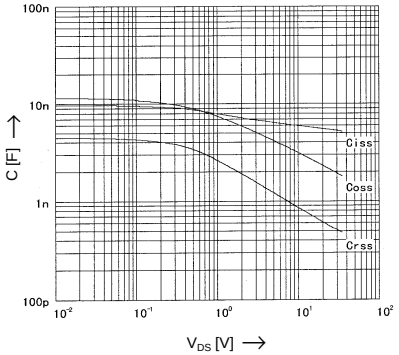
Typical Forward Transconductance vs. I_D
g_{fs}=f(I_D); 80µs pulse test; V_{DS}=25V; T_{ch}=25°C



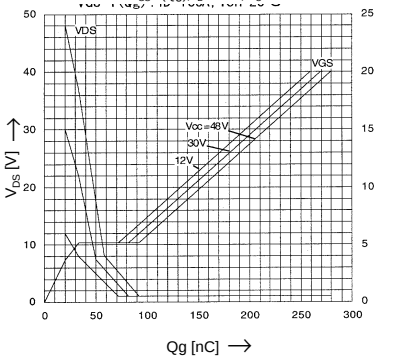
Gate Threshold Voltage vs. T_{ch}
$V_{GS(th)}$=f(T_{ch}); I_D=10mA; V_{DS}=V_{GS}



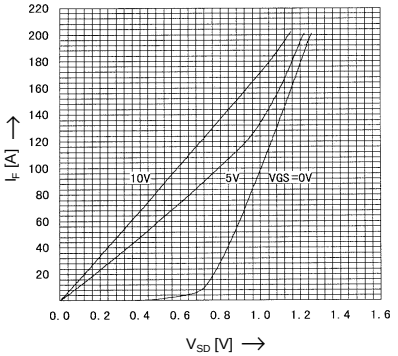
Typical Capacitances vs. V_{DS}
C=f(V_{DS}); V_{GS}=0V; f=1MHz



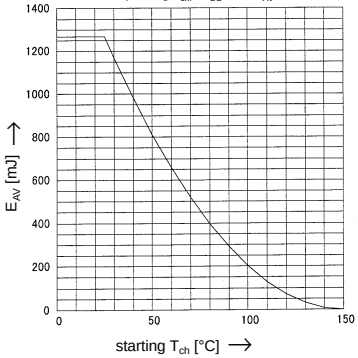
Typical Gate Charge Characteristic
V_{GS}=f(Qg); I_D=100A; T_C=25°C



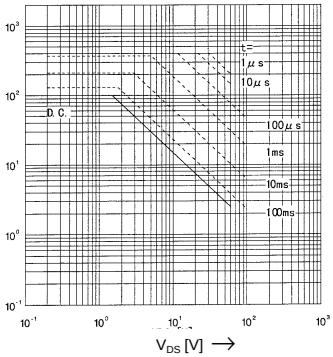
Forward Characteristics of Reverse Diode
I_F=f(V_{SD}); 80µs pulse test; T_{ch}=25°C



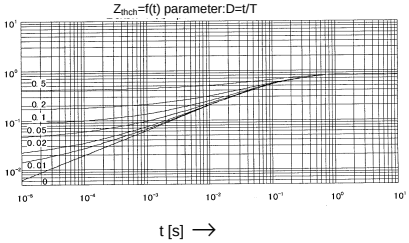
Maximum Avalanche Energy vs. starting T_{ch}
Eas=f(starting T_{ch}): V_{CC}=24V; I_{AV} ≤ 100A



Safe Operation Area
I_D=f(V_{DS}): D=0,01, Tc=25°C

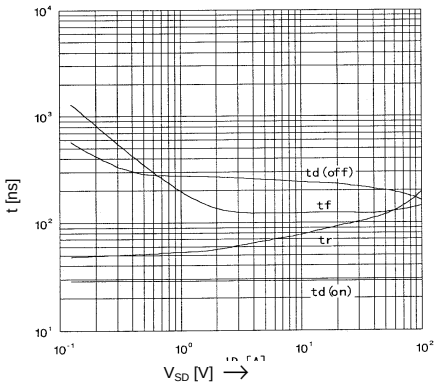


Transient Thermal impedance
$Z_{th(ch-c)}$=f(t) parameter:D=t/T

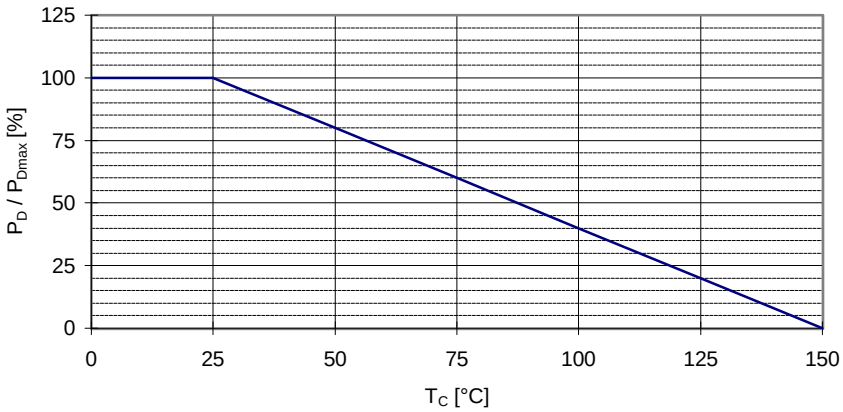


> Characteristics

Typical Switching Characteristics
$t=f(I_D)$: V_{CC} = 30V, V_{GS} = 10V, R_G = 10Ω



Power Dissipation
$P_D=f(T_C)$



Maximum Avalanche Current vs. starting T_{ch}
$I_{AV}=f(\text{starting } T_{ch})$